

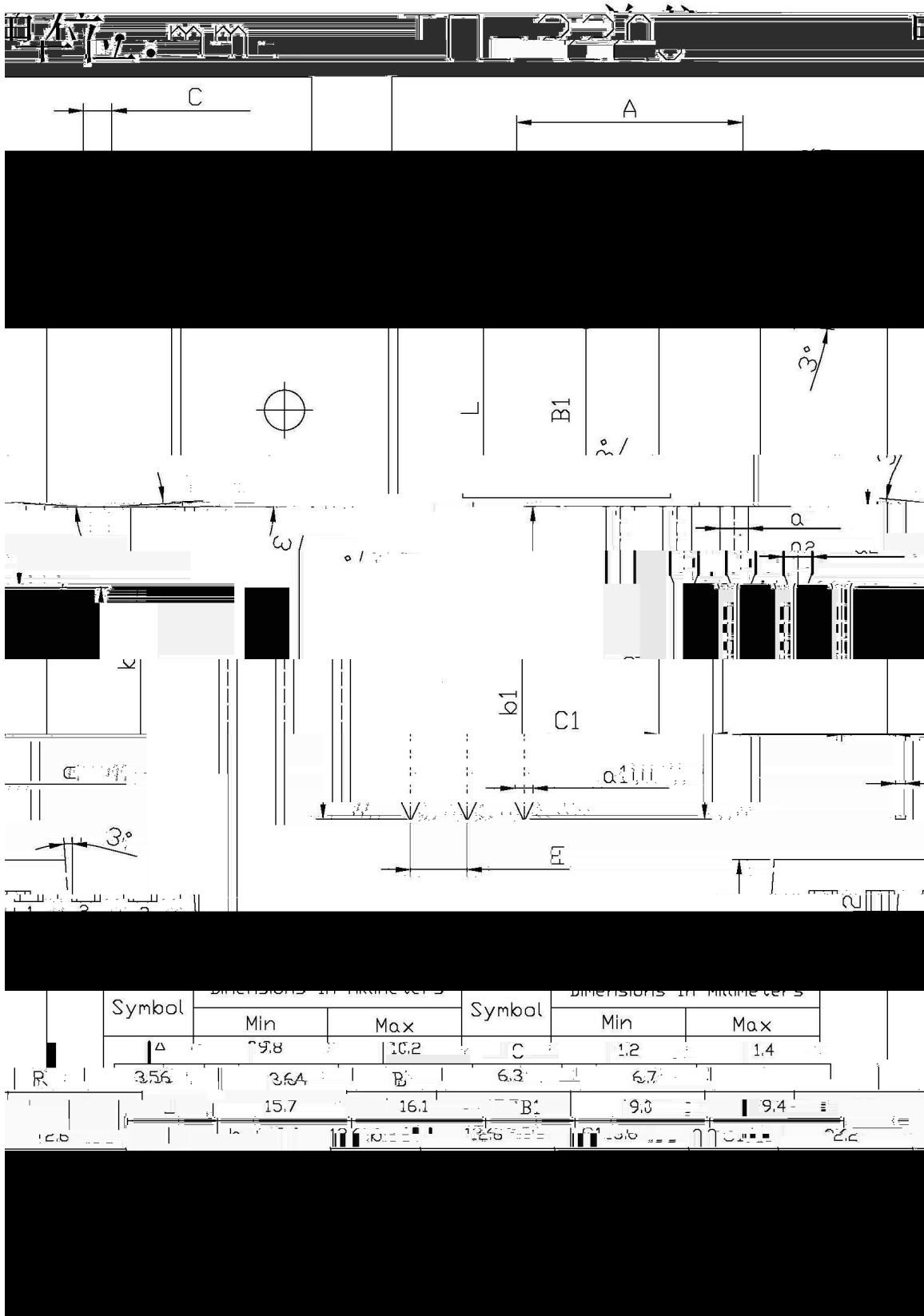
Rev.G Oct.-2018

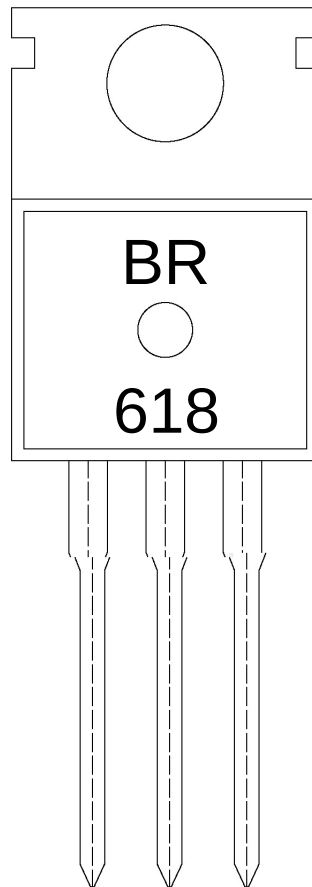
Silicon NPN transistor in a TO-220 Plastic Package.

Built-in resistor at B-E, high voltage.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	250	V
Collector to Emitter Voltage	V_{CEO}	200	V
Emitter to Base Voltage	V_{EBO}	10	V
Collector Current - Continuous	I_C	4.0	A
	$I_{C(Pulse)}$	6.0	A
Base Current - Continuous	I_B	0.5	A
Collector Power Dissipation	$P_C(T_C=25^\circ C)$	40	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=1.0mA$ $I_E=0$	250			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=5.0mA$ $I_B=0$	200			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=180V$ $I_E=0$			1.0	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=10V$ $I_C=0$			1.0	mA
DC Current Gain	h_{FE}	$V_{CE}=5.0V$ $I_C=500mA$	5000			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=2.0A$ $I_B=5.0mA$			1.5	V
	$V_{CE(sat)(2)}$	$I_C=3.0A$ $I_B=20mA$			1.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2.0A$ $I_B=5.0mA$			2.0	V
Transition Frequency	f_T	$V_{CE}=2.0V$ $I_E=1.0A$		8.0		MHz





BR

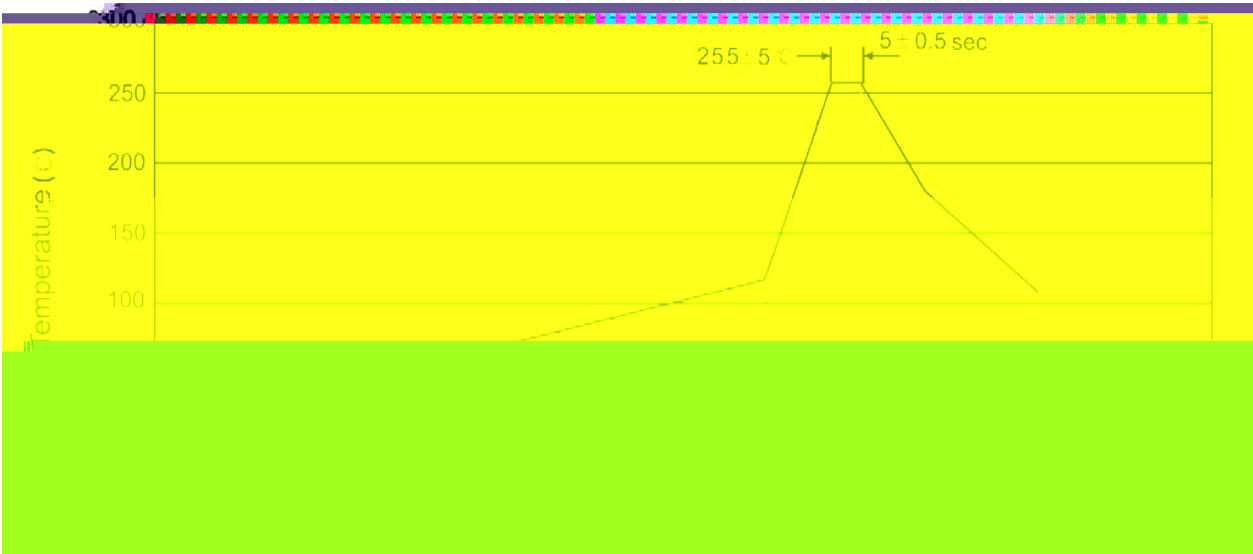
618

Note:

BR: Company Code

618: Product Type.

***: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10 /sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

270 5

10 1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units					Dimension (unit mm ³)		

/ TUBE

Package Type	Units					Dimension (unit mm ³)		